

Supplementary information for: “Band gap
reduction in $\text{InN}_x\text{Sb}_{1-x}$ alloys: optical
absorption, k.P modeling and density functional
theory by W. M. Linhart *et al.*”

The N content in the $\text{InN}_x\text{Sb}_{1-x}$ thin films determined from x-ray diffraction increases with decreasing growth temperature before reaching a plateau at low temperature as shown in Fig. S1.

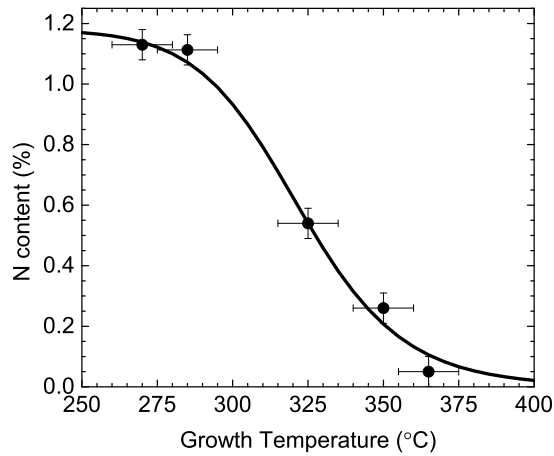


Figure S1: The N content as a function of growth temperature for samples grown at $0.5 \mu\text{mh}^{-1}$ (points) with kinetic modeling (solid line) as described in the main article.

The absorption spectra recorded at 4 K from an InSb substrate and from InNSb/InSb with 0.73% N are shown in Fig. S2. The resulting estimated band gaps are plotted in Fig. 4 of the main article.

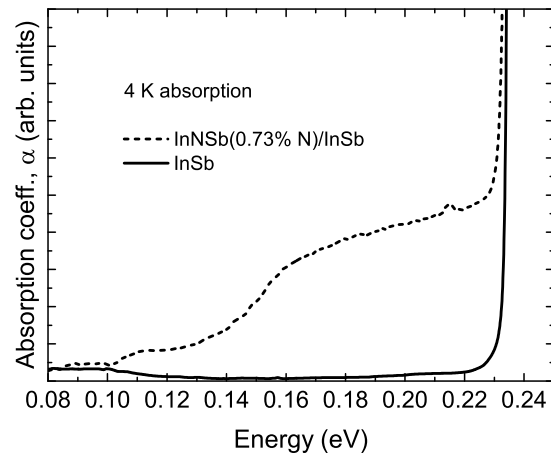


Figure S2: Absorption spectra recorded at 4 K from InSb (solid line) and InNSb/InSb with 0.73% N (dashed line).